PROCESS CP759R

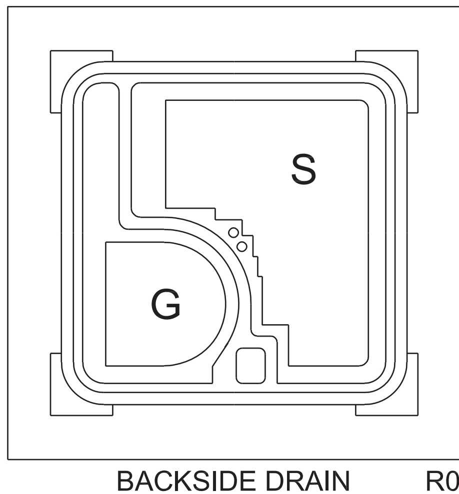
Small Signal MOSFET

P-Channel Enhancement-Mode MOSFET Chip

PROCESS DETAILS

Die Size	9.1 x 9.1 MILS
Die Thickness	3.9 MILS
Gate Bonding Pad Area	2.5 MILS DIAMETER
Source Bonding Pad Area	3.9 x 3.9 MILS
Top Side Metalization	Al-Si - 30,000Å
Back Side Metalization	Au - 12,000Å

GEOMETRY



BACKSIDE DRAIN R0

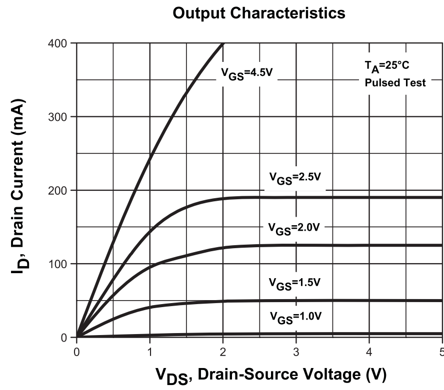
GROSS DIE PER 6 INCH WAFER
290,000

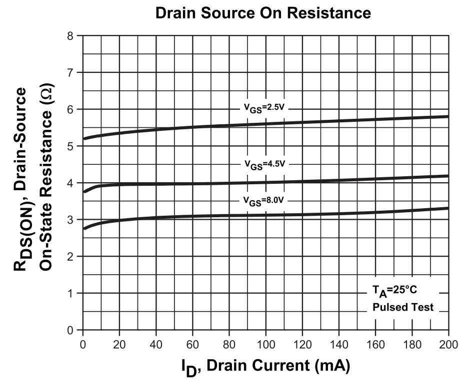
PRINCIPAL DEVICE TYPE
CMRDM7590

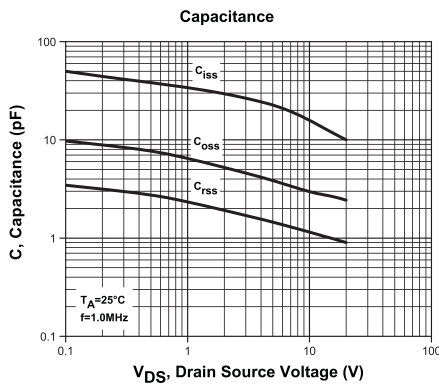
R0 (13-May 2010)

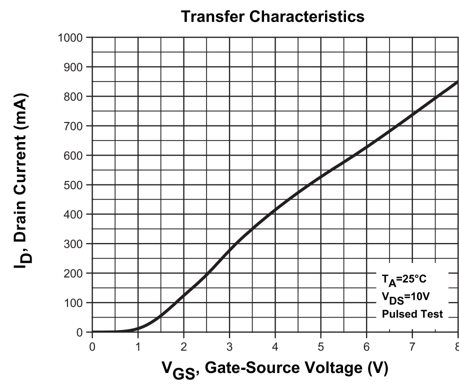
PROCESS CP759R

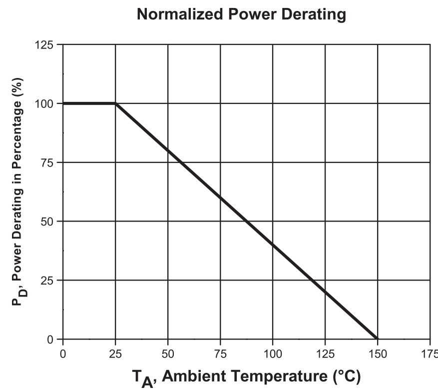
Typical Electrical Characteristics











R0 (13-May 2010)